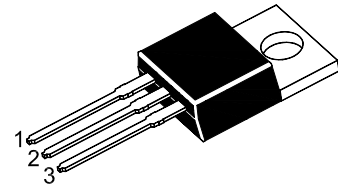


ST H1061

NPN Plastic Power Transistor

Low frequency power amplifier

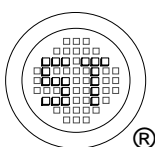


1.Base 2.Collector 3.Emitter

TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Emitter Voltage	V_{CEO}	50	V
Collector Base Voltage	V_{CBO}	50	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	3	A
Power Dissipation	P_{tot}	25	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	-45 to +150	$^\circ\text{C}$



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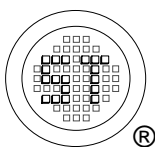


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Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE} = 4\text{ V}$, $I_C = 1\text{ A}$	STH1061A	h_{FE}	35	-	70	-
	STH1061B	h_{FE}	60	-	120	-
	STH1061C	h_{FE}	100	-	200	-
	STH1061D	h_{FE}	160	-	320	-
	at $V_{CE} = 4\text{ V}$, $I_C = 0.1\text{ A}$	h_{FE}	35	-	-	-
Collector Cutoff Current at $V_{CB} = 20\text{ V}$	I_{CBO}	-	-	0.1	mA	
Collector Saturation Voltage at $I_C = 2\text{ A}$, $I_B = 0.2\text{ A}$	$V_{CE(sat)}$	-	-	1	V	
Collector Emitter Breakdown Voltage at $I_C = 50\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V	
Collector Base Breakdown Voltage at $I_C = 5\text{ mA}$	$V_{(BR)CBO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $I_E = 5\text{ mA}$	$V_{(BR)EBO}$	4	-	-	V	
Base Emitter Voltage at $I_C = 1\text{ A}$, $V_{CE} = 4\text{ V}$	V_{BE}	-	-	1.5	V	
Gain Bandwidth Product at $V_{CE} = 4\text{ V}$, $I_C = 0.5\text{ A}$	f_T	-	8	-	MHz	



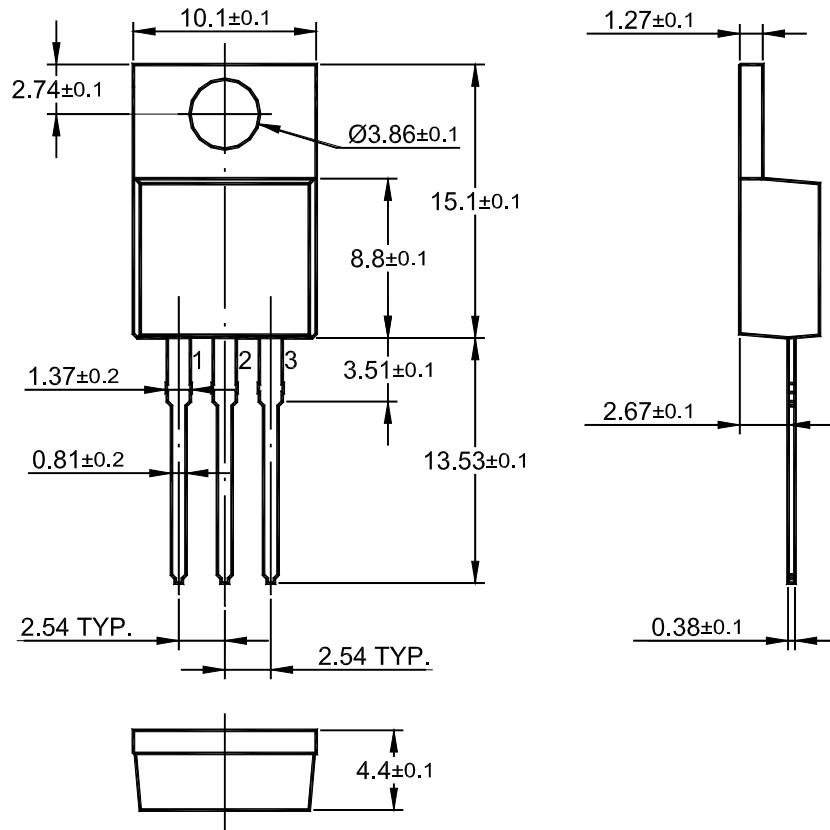
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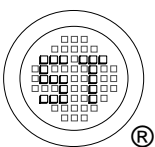
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ST H1061

TO-220 PACKAGE OUTLINE



Dimensions in mm



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